

Patrick Kung

List of Publications by Year in descending order

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81743

39
h-index

102304

66
g-index

167
all docs

167
docs citations

167
times ranked

4121
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrodeposited Transition Metal Dichalcogenides for Use in Hydrogen Evolution Electrocatalysts. <i>Journal of the Electrochemical Society</i> , 2022, 169, 026510.	1.3	6
2	Nanoscale Raman Characterization of a 2D Semiconductor Lateral Heterostructure Interface. <i>ACS Nano</i> , 2022, 16, 340-350.	7.3	9
3	Theoretical Analysis of the Nanoscale Composition, Tip-Enhanced Raman Spectroscopy, and Electronic Properties of Alloys in 2D MoS ₂ WS ₂ Heterostructures. <i>Journal of Physical Chemistry C</i> , 2022, 126, 9099-9108.	1.5	4
4	In Situ Thermomechanical Loading for TEM Studies of Nanocrystalline Alloys. <i>Microscopy and Microanalysis</i> , 2021, 27, 2420-2424.	0.2	0
5	Forbidden and Second-Order Phonons in Raman Spectra of Single and Few-Layer MoS ₂ Close to C Exciton Resonance. <i>Journal of Physical Chemistry C</i> , 2021, 125, 23904-23910.	1.5	13
6	Breast cancer biomarker detection through the photoluminescence of epitaxial monolayer MoS ₂ flakes. <i>Scientific Reports</i> , 2020, 10, 16039.	1.6	33
7	Structural and mechanical characterization of carbon fibers grown by laser induced chemical vapor deposition at hyperbaric pressures. <i>Carbon</i> , 2020, 162, 95-105.	5.4	10
8	Investigating the Redox Properties of Two-Dimensional MoS ₂ Using Photoluminescence Spectroelectrochemistry and Scanning Electrochemical Cell Microscopy. <i>Journal of Physical Chemistry Letters</i> , 2020, 11, 3488-3494.	2.1	35
9	Photoluminescence enhancement of monolayer MoS ₂ using plasmonic gallium nanoparticles. <i>Nanoscale Advances</i> , 2019, 1, 884-893.	2.2	33
10	Polarization dependent trion dynamics in large area CVD grown 2D monolayer MoS ₂ by terahertz time-domain spectroscopy. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 155104.	1.3	2
11	Al doping in ZnO nanowires enhances ultraviolet emission and suppresses broad defect emission. <i>Journal of Luminescence</i> , 2019, 211, 264-270.	1.5	12
12	Monolayer MoS ₂ field-effect transistors patterned by photolithography for active matrix pixels in organic light-emitting diodes. <i>Npj 2D Materials and Applications</i> , 2019, 3, .	3.9	43
13	Ultra-High Efficiency and Broad Band Operation of Infrared Metasurface Anomalous Reflector based on Graphene Plasmonics. <i>Scientific Reports</i> , 2019, 9, 1249.	1.6	13
14	Observation of Broadband Electrically Tunable THz Metamaterials Polarization Conversion. , 2019, , .		0
15	Synthesis of MoS ₂ from [Mo ₃ S ₇ (S ₂ CNEt ₂) ₃] for enhancing photoelectrochemical performance and stability of Cu ₂ O photocathode toward efficient solar water splitting. <i>Journal of Materials Chemistry A</i> , 2018, 6, 9569-9582.	5.2	33
16	Electrically Tunable THz Polarization Conversion in Liquid Crystal Metamaterials. , 2018, , .		0
17	Strong Solar Radiation Forces from Anomalous Reflecting Metasurfaces for Solar Sail Attitude Control. <i>Scientific Reports</i> , 2018, 8, 10026.	1.6	27
18	Investigation of tunable terahertz metamaterial perfect absorber with anisotropic dielectric liquid crystal. <i>AIP Advances</i> , 2017, 7, .	0.6	17

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19	High Efficient THz Emission From Unbiased and Biased Semiconductor Nanowires Fabricated Using Electron Beam Lithography. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-7.	1.9	5
20	Review on Polarization Selective Terahertz Metamaterials: from Chiral Metamaterials to Stereometamaterials. Journal of Infrared, Millimeter, and Terahertz Waves, 2017, 38, 1047-1066.	1.2	28
21	A Facile Electrochemical Reduction Method for Improving Photocatalytic Performance of Fe_2O_3 Photoanode for Solar Water Splitting. ACS Applied Materials & Interfaces, 2017, 9, 381-390.	4.0	51
22	(Invited) Transition Metal Dichalcogenide Semiconductor Growth and Large Area Devices for Optoelectronics and Sensing. ECS Transactions, 2017, 80, 1-11.	0.3	4
23	Independent component analysis applications on THz sensing and imaging. , 2016, , .		0
24	Biased THz emission from InGaAs nanowires fabricated using electron beam lithography. , 2016, , .		0
25	Slowing terahertz wave using thin flexible metamaterials. , 2016, , .		0
26	Thickness identification of epitaxial Bi_2Te_3 via optical contrast. 2D Materials, 2016, 3, 021010.	2.0	13
27	Investigation of robust flexible conformal THz perfect metamaterial absorber. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	18
28	Terahertz metamaterials: design, implementation, modeling and applications. Proceedings of SPIE, 2016, , .	0.8	0
29	Terahertz devices, spectroscopy, and signal processing for biosensing. Proceedings of SPIE, 2016, , .	0.8	0
30	Analytical simulation of RBS spectra of nanowire samples. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 116-120.	0.6	9
31	Liquid Crystal Frequency Tunable Terahertz Metamaterial Absorber. , 2016, , .		1
32	Slow Light by Hybridized Double Split Ring Resonators. , 2016, , .		0
33	Impact of Substrate and Bright Resonances on Group Velocity in Metamaterial without Dark Resonator. Scientific Reports, 2015, 5, 14373.	1.6	26
34	Plasmon-Induced Transparency by Hybridizing Concentric-Twisted Double Split Ring Resonators. Scientific Reports, 2015, 5, 15735.	1.6	56
35	Slow light by hybridized concentric-twisted double split ring resonators and THz application. , 2015, , .		0
36	THz emission from InP and InGaAs nanowires fabricated using electron beam lithography. , 2015, , .		1

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37	Spectroscopic Characteristics of Three Dimensional Split-Ring Resonator Arrays at Terahertz Frequencies. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 2289-2293.	0.9	1
38	Continuous-flow system and monitoring tools for the dielectrophoretic integration of nanowires in light sensor arrays. <i>Nanotechnology</i> , 2015, 26, 115502.	1.3	3
39	Low Leakage Current ZnO Nanowire Schottky Photodiodes Built by Dielectrophoretic Contact. <i>IEEE Electron Device Letters</i> , 2015, 36, 814-816.	2.2	8
40	Exciton-exciton scattering in vapor phase ZnO nanoparticles. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	13
41	Comprehensive study of terahertz metamaterial absorber by applying a hybrid approach on its circuit analogue. <i>Optical Materials Express</i> , 2015, 5, 1772.	1.6	12
42	Investigation of high frequency carrier dynamics of Al-doped ZnO nanowires by terahertz time domain spectroscopy. , 2014, , .		1
43	Surface optical phonons in GaAs nanowires grown by Ga-assisted chemical beam epitaxy. <i>Journal of Applied Physics</i> , 2014, 115, 034307.	1.1	20
44	Synthesis and Optical Properties of Undoped and Aluminum Doped ZnO Nanowires for Optoelectronic Nanodevice Applications. , 2014, , .		0
45	Investigation of silicon-germanium nanowires THz emission. , 2014, , .		3
46	Polarization controllable THz stereometamaterial absorber. , 2014, , .		2
47	Effect of pressure and Al doping on structural and optical properties of ZnO nanowires synthesized by chemical vapor deposition. <i>Journal of Luminescence</i> , 2014, 146, 470-474.	1.5	37
48	Enhanced fabrication process of zinc oxide nanowires for optoelectronics. <i>Thin Solid Films</i> , 2014, 555, 42-47.	0.8	18
49	Polarization-Dependent, Frequency-Selective THz Stereometamaterial Perfect Absorber. <i>Physical Review Applied</i> , 2014, 1, .	1.5	44
50	Nanotechnology in Electronics. , 2014, , 17-36.		2
51	Growth, doping, and characterization of ZnO nanowire arrays. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, .	0.6	11
52	Direct Measurement of Band Edge Discontinuity in Individual Core-Shell Nanowires by Photocurrent Spectroscopy. <i>Nano Letters</i> , 2013, 13, 4152-4157.	4.5	12
53	Observation of Hydrofluoric Acid Burns on Osseous Tissues by Means of Terahertz Spectroscopic Imaging. <i>IEEE Transactions on Terahertz Science and Technology</i> , 2013, 3, 387-394.	2.0	12
54	Equivalent-Circuit Interpretation of the Polarization Insensitive Performance of THz Metamaterial Absorbers. <i>IEEE Transactions on Terahertz Science and Technology</i> , 2013, 3, 846-850.	2.0	40

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55	Pure zincblende GaAs nanowires grown by Ga-assisted chemical beam epitaxy. Journal of Crystal Growth, 2013, 372, 205-212.	0.7	13
56	Conducting properties of nearly depleted ZnO nanowire UV sensors fabricated by dielectrophoresis. Nanotechnology, 2013, 24, 415702.	1.3	16
57	Aperture-less terahertz near-field imaging. Proceedings of SPIE, 2013, , .	0.8	0
58	Effects of saline on terahertz absorption of aqueous glucose at physiological concentrations probed by THz spectroscopy. , 2013, , .		2
59	Observation of Hydrofluoric Acid Burns on Osseous Tissues by Means of Terahertz Spectroscopic Imaging. IEEE Journal of Biomedical and Health Informatics, 2013, 17, 798-805.	3.9	10
60	Theoretical and experimental investigation of hybrid broadband terahertz metamaterial absorber. Proceedings of SPIE, 2013, , .	0.8	3
61	Design and analysis of perfect terahertz metamaterial absorber by a novel dynamic circuit model. Optics Express, 2013, 21, 16455.	1.7	46
62	Atom probe tomography of AlInN/GaN HEMT structures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, .	0.6	10
63	Terahertz metamaterials perfect absorbers for sensing and imaging. Proceedings of SPIE, 2013, , .	0.8	11
64	Identification of tissue interaction of terahertz radiation toward functional tissue imaging. , 2013, , .		1
65	Identification of tissue interaction of terahertz radiation toward functional tissue imaging by terahertz spectroscopic imaging. , 2013, , .		2
66	Analysis of terahertz metamaterial perfect absorber by using a novel quasi-static RLC circuit model. , 2013, , .		0
67	Voltage and Laser-Assisted Mode Atom Probe Tomography of Gallium Nitride. Microscopy and Microanalysis, 2013, 19, 990-991.	0.2	0
68	Photovoltaic devices based on quantum dot functionalized nanowire arrays embedded in an organic matrix. Proceedings of SPIE, 2012, , .	0.8	0
69	Design, simulation, and characterization of THz metamaterial absorber. , 2012, , .		3
70	Characteristics of THz carrier dynamics in GaN thin film and ZnO nanowires by temperature dependent terahertz time domain spectroscopy measurement. Solid-State Electronics, 2012, 78, 68-74.	0.8	23
71	Comparative reconstructions of THz spectroscopic imaging for non-destructive testing and biomedical imaging. , 2012, , .		3
72	Highly efficient, polarization insensitive terahertz metamaterial perfect absorber and imaging. , 2012, , .		0

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73	Atom Probe Tomography of Zinc Oxide Nanowires. Journal of Electronic Materials, 2012, 41, 801-808.	1.0	24
74	Highly Efficient, Polarization Insensitive Terahertz Metamaterial Perfect Absorber and Imaging. , 2012, , .		0
75	Terahertz spectroscopic properties of three-dimensional split-ring resonator arrays. , 2011, , .		0
76	Application of terahertz spectral imaging for the identification of osseous tissue. , 2011, , .		1
77	Temperature dependent THz time-domain spectroscopy of carrier dynamics in GaN thin film. , 2011, , .		1
78	High sensitivity and high selectivity terahertz biomedical imaging (Invited Paper). Chinese Optics Letters, 2011, 9, 110009-110012.	1.3	5
79	Quantum dot functionalized ZnO nanowire/P3HT hybrid photovoltaic devices. , 2011, , .		0
80	Design, simulation, and characterization of THz metamaterial absorber. , 2011, , .		2
81	High Resolution, Two-Dimensional Image Mapping of ZnO Nanowires by Confocal MicroPhotoluminescence and MicroRaman Spectroscopy. Journal of Nanoscience and Nanotechnology, 2011, 11, 5898-5903.	0.9	1
82	InP/ZnS core-shell quantum dots sensitized ZnO nanowires for photovoltaic devices. , 2011, , .		2
83	Hybrid nanostructures based on quantum dots and nanowires. , 2011, , .		0
84	Nanoscale characteristics of single crystal zinc oxide nanowires. , 2011, , .		4
85	Eu ²⁺ →Mn ²⁺ energy transfer in white-light-emitting T-phase (Ba,Ca) ₂ SiO ₄ :Eu ²⁺ , Mn ²⁺ phosphor. Journal of Luminescence, 2010, 130, 560-566.	1.5	42
86	Thermally stable deep-blue Ba _{1.2} Ca _{0.8} SiO ₄ :Ce ³⁺ phosphor for white-light-emitting diode. Journal of Luminescence, 2010, 130, 1292-1294.	1.5	18
87	White-light generation through Ce ³⁺ /Mn ²⁺ -codoped and Eu ²⁺ -doped Ba _{1.2} Ca _{0.8} SiO ₄ T-phase phosphors. Journal of Luminescence, 2010, 130, 2442-2445.	1.5	17
88	Temperature and excitation power-resistant white-light emission of the -phase phosphor. Solid State Communications, 2010, 150, 329-332.	0.9	14
89	Blue-emitting Sr ₃ Ga ₂ O ₅ Cl ₂ :Eu ²⁺ phosphor for white-light-emitting diode. , 2010, , .		1
90	Super-bright and short-lived photoluminescence of textured Zn ₂ SiO ₄ :Mn ²⁺ phosphor film on quartz glass. , 2010, , .		0

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91	Excellent Brightness with Shortening Lifetime of Textured Zn ₂ SiO ₄ :Mn ²⁺ +Phosphor Films on Quartz Glass. Japanese Journal of Applied Physics, 2010, 49, 042603.	0.8	1
92	New Green Phosphor (Ba _{1.2} Ca _{0.8-x} Eu _x)SiO ₄ for White-Light-Emitting Diode. Japanese Journal of Applied Physics, 2010, 49, 020214.	0.8	10
93	White-light generation through Ce ³⁺ /Mn ²⁺ -codoped and Eu ²⁺ -doped Ba _{1.2} Ca _{0.8-x} SiO ₄ T-phase phosphors. , 2010, , .		0
94	Acquisition and analysis of Terahertz Time Domain imaging and sensing. , 2010, , .		2
95	Synthesis and Optical Properties of ZnO Nanowires for Nanophotonics. , 2010, , .		0
96	Synthesis and optical properties of ZnO nanowires for nanophotonics. , 2010, , .		0
97	Optical Properties of Closely Coupled Dilute Nitride Mid-Infrared InNSb Quantum Dots. , 2008, , .		0
98	Geiger-mode operation of back-illuminated GaN avalanche photodiodes. Applied Physics Letters, 2007, 91, .	1.5	40
99	Hole-initiated multiplication in back-illuminated GaN avalanche photodiodes. Applied Physics Letters, 2007, 90, 141112.	1.5	95
100	Scaling in back-illuminated GaN avalanche photodiodes. Applied Physics Letters, 2007, 91, .	1.5	33
101	III-nitride avalanche photodiodes. , 2007, , .		7
102	Etching of ZnO towards the development of ZnO homostructure LEDs. , 2007, , .		2
103	Materials characterization of n - ZnO / p - GaN : Mg / c - Al ₂ O ₃ UV LEDs grown by pulsed laser deposition and metal-organic chemical vapor deposition. Superlattices and Microstructures, 2007, 42, 322-326.	1.4	15
104	Electroluminescence at 375nm from a ZnO [∞] GaN:Mg [∞] c-Al ₂ O ₃ heterojunction light emitting diode. Applied Physics Letters, 2006, 88, 141918.	1.5	170
105	Fabrication of GaN nanotubular material using MOCVD with aluminum oxide membrane. , 2006, 6127, 123.		0
106	Investigations of p-type signal for ZnO thin films grown on (100) GaAs substrates by pulsed laser deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1038-1041.	0.8	16
107	Solar-blind avalanche photodiodes. , 2006, , .		1
108	Fabrication of GaN nanotubular material using MOCVD with an aluminium oxide membrane. Nanotechnology, 2006, 17, 54-59.	1.3	52

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109	Back-illuminated solar-blind photodetectors for imaging applications. , 2005, 5732, 175.		8
110	Short-wavelength ultraviolet light-emitting diodes based on AlGaIn. , 2005, , .		0
111	The Rise of III-nitrides: An Introduction. , 2005, , 9-22.		3
112	ZnO thin film templates for GaN-based devices. , 2005, , .		21
113	AlGaIn-based deep UV light emitting diodes with peak emission below 255 nm. , 2005, , .		0
114	Avalanche multiplication in AlGaIn based solar-blind photodetectors. Applied Physics Letters, 2005, 87, 241123.	1.5	93
115	320Å–256 solar-blind focal plane arrays based on Al _x Ga _{1-x} N. Applied Physics Letters, 2005, 86, 011117.	1.5	66
116	High-power 280 nm AlGaIn light-emitting diodes based on an asymmetric single-quantum well. Applied Physics Letters, 2004, 84, 1046-1048.	1.5	165
117	High quantum efficiency AlGaIn solar-blind p-i-n photodiodes. Applied Physics Letters, 2004, 84, 1248-1250.	1.5	121
118	Review of III-nitride optoelectronic materials for light emission and detection. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, S141-S148.	0.8	8
119	High-quantum-efficiency solar-blind photodetectors. , 2004, , .		17
120	Growth of deep-UV light-emitting diodes by metalorganic chemical vapor deposition. , 2004, , .		1
121	Photoluminescence study of AlGaIn-based 280 nm ultraviolet light-emitting diodes. Applied Physics Letters, 2003, 83, 4083-4085.	1.5	72
122	4.5 mW operation of AlGaIn-based 267 nm deep-ultraviolet light-emitting diodes. Applied Physics Letters, 2003, 83, 4701-4703.	1.5	124
123	Characteristics of high-quality p-type Al _x Ga _{1-x} N/GaN superlattices. Applied Physics Letters, 2002, 80, 2108-2110.	1.5	21
124	Comparison of ultraviolet light-emitting diodes with peak emission at 340 nm grown on GaN substrate and sapphire. Applied Physics Letters, 2002, 81, 2151-2153.	1.5	56
125	Future of Al _x Ga _{1-x} N materials and device technology for ultraviolet photodetectors. , 2002, , .		31
126	Top-emission ultraviolet light-emitting diodes with peak emission at 280 nm. Applied Physics Letters, 2002, 81, 801-802.	1.5	91

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127	Morphological characterization of selectively overgrown GaN via lateral epitaxy. Journal of Materials Science, 2002, 37, 1951-1957.	1.7	0
128	<title>Al<formula><inf><roman>x</roman></inf></formula>Ga<formula><inf><roman>1-x</roman></inf></formula>N materials and device technology for solar blind ultraviolet photodetector applications</title>. , 2001, , .		13
129	Al Ga1 ^x N for solar-blind UV detectors. Journal of Crystal Growth, 2001, 231, 366-370.	0.7	106
130	Lateral epitaxial overgrowth of GaN on sapphire and silicon substrates for ultraviolet photodetector applications. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 74, 107-112.	1.7	12
131	Solar-blind Al x Ga 1-x N p-i-n photodetectors grown on LEO and non-LEO GaN. , 2000, 3948, 265.		10
132	Solar-blind AlGa _N photodiodes with very low cutoff wavelength. Applied Physics Letters, 2000, 76, 403-405.	1.5	166
133	Pulse autocorrelation measurements based on two- and three-photon conductivity in a GaN photodiode. Applied Physics Letters, 1999, 75, 3778-3780.	1.5	62
134	High-speed, low-noise metal- ^{semiconductor} -metal ultraviolet photodetectors based on GaN. Applied Physics Letters, 1999, 74, 762-764.	1.5	175
135	Lateral epitaxial overgrowth of GaN films on sapphire and silicon substrates. Applied Physics Letters, 1999, 74, 570-572.	1.5	73
136	High-quality visible-blind AlGa _N p-i-n photodiodes. Applied Physics Letters, 1999, 74, 1171-1173.	1.5	145
137	Phase-matched optical second-harmonic generation in GaN and AlN slab waveguides. Journal of Applied Physics, 1999, 85, 2497-2501.	1.1	31
138	Schottky MSM photodetectors on GaN films grown on sapphire by lateral epitaxial overgrowth. , 1999, , .		6
139	Aluminum gallium nitride short-period superlattices doped with magnesium. Applied Physics Letters, 1999, 74, 2023-2025.	1.5	57
140	Band-gap narrowing and potential fluctuation in Si-doped GaN. Applied Physics Letters, 1999, 74, 102-104.	1.5	88
141	Visible blind GaN p-i-n photodiodes. Applied Physics Letters, 1998, 72, 3303-3305.	1.5	112
142	GaN/Ga _N Multi-Quantum Well Laser Diodes Grown by Low-Pressure Metalorganic Chemical Vapor Deposition. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	38
143	Continuous-wave room-temperature operation of InGa _N /Ga _N multiquantum well lasers grown by low-pressure metalorganic chemical vapor deposition. , 1998, , .		2
144	<title>GaN p-i-n photodiodes with high visible-to-ultraviolet rejection ratio</title>. , 1998, 3287, 214.		8

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145	Determination of the band-gap energy of Al _{1-x} In _x N grown by metal-organic chemical-vapor deposition. Applied Physics Letters, 1997, 71, 800-802.	1.5	119
146	Al _x Ga _{1-x} N (0 ≤ x ≤ 1) ultraviolet photodetectors grown on sapphire by metal-organic chemical-vapor deposition. Applied Physics Letters, 1997, 70, 949-951.	1.5	113
147	<title>Recent advances in III-nitride materials, characterization and device applications</title> ., 1997, ,		1
148	Comparison of trimethylgallium and triethylgallium for the growth of GaN. Applied Physics Letters, 1997, 71, 3272-3274.	1.5	41
149	MOCVD growth of high quality GaN—AlGaN based structures on Al ₂ O ₃ substrates with dislocation density less than 10 ⁷ cm ⁻² . Journal of the European Ceramic Society, 1997, 17, 1781-1785.	2.8	4
150	Morphology of twinned GaN grown on (11 $\bar{1}$:0) sapphire substrates. Solid-State Electronics, 1997, 41, 227-229.	0.8	6
151	AlGa _x N ultraviolet photoconductors grown on sapphire. Applied Physics Letters, 1996, 68, 2100-2101.	1.5	171
152	High Resolution X-ray Diffraction of GaN Grown on Sapphire Substrates. Materials Research Society Symposia Proceedings, 1996, 449, 477.	0.1	7
153	Al _x Ga _{1-x} N-Based Materials and Heterostructures. Materials Research Society Symposia Proceedings, 1996, 449, 79.	0.1	15
154	Metalorganic chemical vapor deposition of monocrystalline GaN thin films on β -LiGaO ₂ substrates. Applied Physics Letters, 1996, 69, 2116-2118.	1.5	67
155	Observation of room temperature surface-emitting stimulated emission from GaN:Ge by optical pumping. Journal of Applied Physics, 1996, 80, 6544-6546.	1.1	18
156	Observation of inversion layers at AlN-Si interfaces fabricated by metal organic chemical vapour deposition. Electronics Letters, 1996, 32, 1622.	0.5	12
157	Spectral Response of GaN P-N Junction Photovoltaic Structures. Materials Research Society Symposia Proceedings, 1995, 395, 955.	0.1	3
158	Growth of GaN without Yellow Luminescence. Materials Research Society Symposia Proceedings, 1995, 395, 625.	0.1	25
159	Photovoltaic effects in GaN structures with p-n junctions. Applied Physics Letters, 1995, 67, 2028-2030.	1.5	78
160	Kinetics of photoconductivity in n-type GaN photodetector. Applied Physics Letters, 1995, 67, 3792-3794.	1.5	77
161	Growth of Al _x Ga _{1-x} N:Ge on sapphire and silicon substrates. Applied Physics Letters, 1995, 67, 1745-1747.	1.5	90
162	High quality AlN and GaN epilayers grown on (00 $\bar{1}$:1) sapphire, (100), and (111) silicon substrates. Applied Physics Letters, 1995, 66, 2958-2960.	1.5	175

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163	Photoluminescence Study of GaN. Acta Physica Polonica A, 1995, 88, 601-606.	0.2	22
164	Thermal stability of GaN thin films grown on (0001) Al ₂ O ₃ , (011 $\bar{1}$,2) Al ₂ O ₃ and (0001)Si ₆ H ₆ SiC substrates. Journal of Applied Physics, 1994, 76, 236-241.	1.1	89
165	High quality aluminum nitride epitaxial layers grown on sapphire substrates. Applied Physics Letters, 1994, 64, 339-341.	1.5	100
166	A crystallographic model of (00 $\bar{1}$) aluminum nitride epitaxial thin film growth on (00 $\bar{1}$) sapphire substrate. Journal of Applied Physics, 1994, 75, 3964-3967.	1.1	104
167	Crystallography of epitaxial growth of wurtzite-type thin films on sapphire substrates. Journal of Applied Physics, 1994, 75, 4515-4519.	1.1	89